

<b>SANYO</b>	No.4568A	<b>2SK2151</b>
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

**Absolute Maximum Ratings at Ta = 25°C**

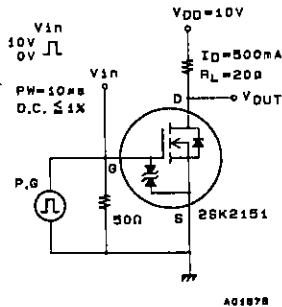
			unit
Drain-to-Source Voltage	V <sub>DS</sub>	20	V
Gate-to-Source Voltage	V <sub>GS</sub>	±15	V
Drain Current(DC)	I <sub>D</sub>	1	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1%	4 A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> = 25°C	3.5 W
		Mounted on ceramic board (250mm <sup>2</sup> × 0.8mm)	1.3 W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	20			V
G-S Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> = ±100μA, V <sub>DS</sub> = 0	±15			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0			100	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 500mA	0.6	1		S
Static Drain-to-Source ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 500mA, V <sub>GS</sub> = 10V		350	480	mΩ
ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 500mA, V <sub>GS</sub> = 4V		550	750	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, f = 1MHz		50		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 10V, f = 1MHz		45		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10V, f = 1MHz		15		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		8		ns
Rise Time	t <sub>r</sub>	"		10		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		30		ns
Fall Time	t <sub>f</sub>	"		20		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0		1.0		V

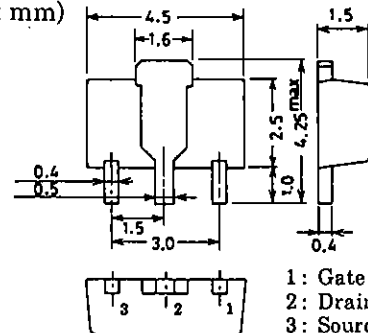
Marking : KI

**Switching Time Test Circuit**



**Package Dimensions 2062A**

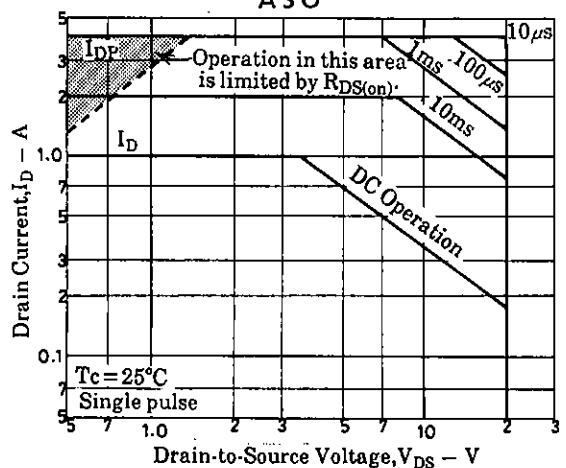
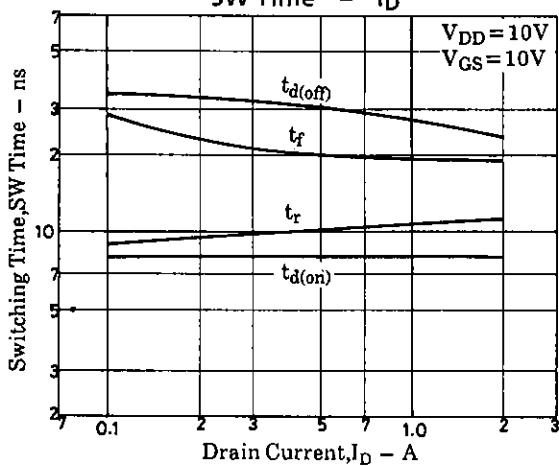
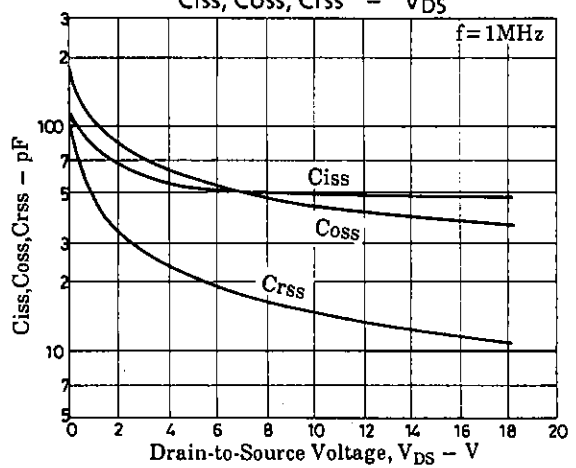
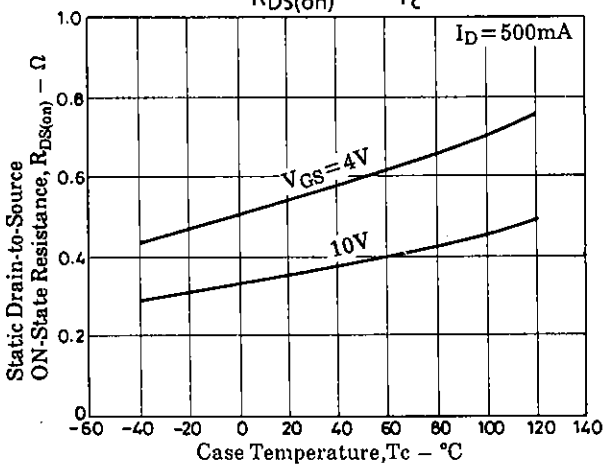
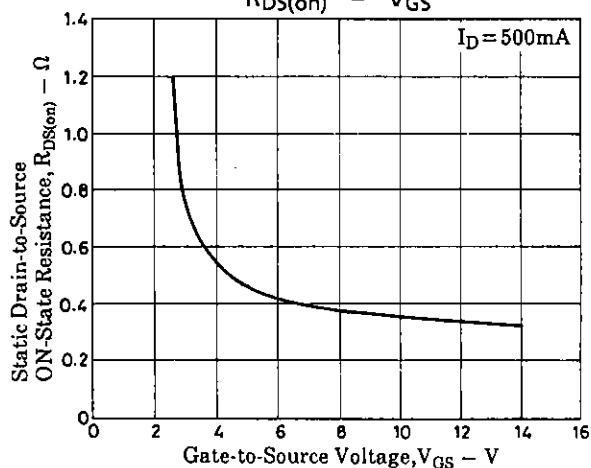
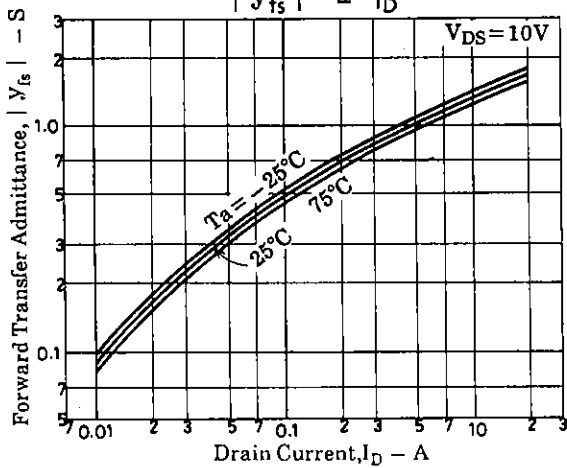
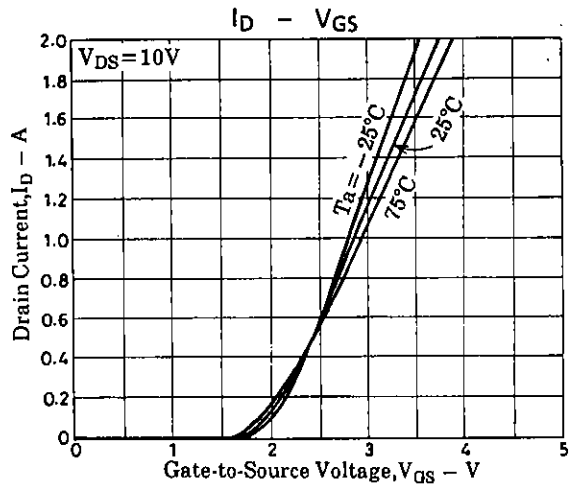
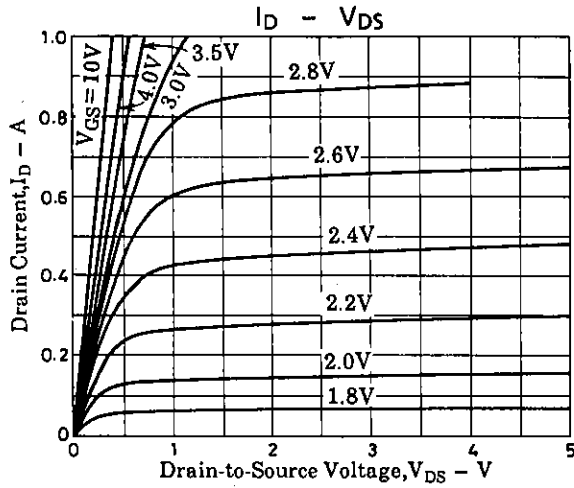
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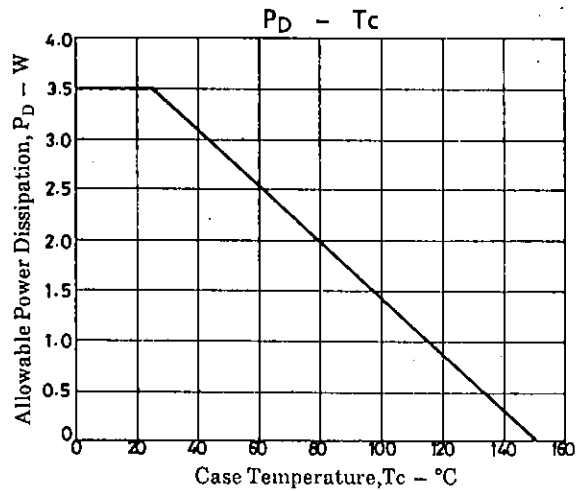
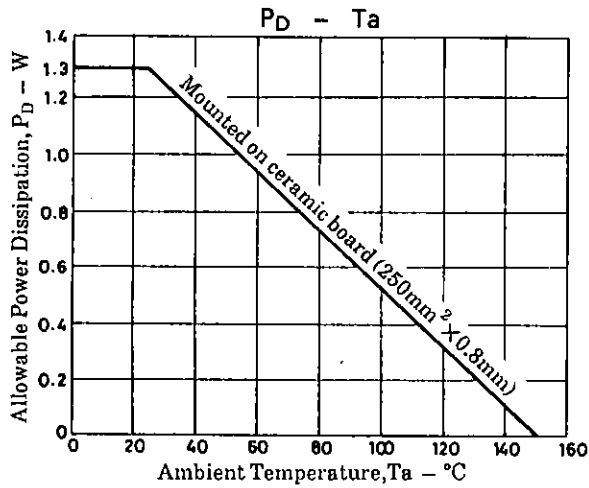


1: Gate  
2: Drain  
3: Source  
SANYO:PCP  
(Bottom View)

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